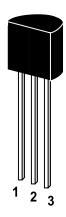
### **PNP Silicon Epitaxial Planar Transistor**

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into three groups, G, H and I, according to its DC current gain. As complementary type the NPN transistor ST 9013 is recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

### Absolute Maximum Ratings ( $T_a = 25$ °C)

	Symbol	Value	Unit
Collector Emitter Voltage	-V <sub>CEO</sub>	30	V
Emitter Base Voltage	-V <sub>EBO</sub>	5	V
Collector Current	-I <sub>C</sub>	800	mA
Peak Collector Current	-I <sub>CM</sub>	1	А
Base Current	-I <sub>B</sub>	100	mA
Power Dissipation	P <sub>tot</sub>	625 <sup>1)</sup>	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	Ts	-55 to +150	°C
1) Valid provided that leads are kept at ambig	ent temperature at a distanc	re of 2 mm from case	•









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## Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V <sub>CE</sub> =1V, -I <sub>C</sub> =50mA					
Current Gain Group G	h <sub>FE</sub>	110	-	183	-
н	h <sub>FE</sub>	177	-	250	-
I	h <sub>FE</sub>	250	-	380	-
at -V <sub>CE</sub> =1V, -I <sub>C</sub> =500mA	h <sub>FE</sub>	40	-	-	-
Collector Cutoff Current					
at -V <sub>CB</sub> =31V	-I <sub>CBO</sub>	-	-	100	nA
Collector Emitter Breakdown Voltage					
at -I <sub>C</sub> =1mA	-V <sub>(BR)CEO</sub>	30	-	-	V
Emitter Base Cutoff Current					
at -V <sub>EB</sub> =5.1V	-I <sub>EBO</sub>	-	-	100	nA
Collector Saturation Voltage					
at -I <sub>C</sub> =500mA, -I <sub>B</sub> =20mA	-V <sub>CE(sat)</sub>	-	-	0.7	V
Base Saturation Voltage					
at -I <sub>C</sub> =500mA, -I <sub>B</sub> =20mA	-V <sub>BE(sat)</sub>	-	-	1.2	V
Base Emitter Voltage					
at -V <sub>CE</sub> =1V, -I <sub>C</sub> =50mA	-V <sub>BE</sub>	0.6	-	0.75	V
Gain Bandwidth Product					
at -V <sub>CE</sub> =5V, -I <sub>C</sub> =10mA, f=50MHz	f <sub>T</sub>	-	100	-	MHz
Collector Base Capacitance					
at -V <sub>CB</sub> =10V, f=1MHz	C <sub>CBO</sub>		12	-	pF
Thermal Resistance Junction to Ambient	R <sub>thA</sub>	-	-	200 <sup>1)</sup>	K/W
1) Valid provided that leads are kept at ambient to	emperature a	t a distance	of 2 mm fron	n case	







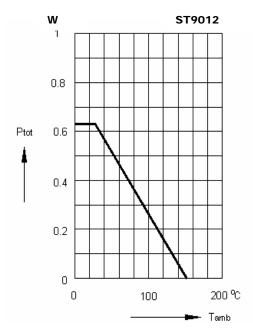




#### Admissible power dissipation

### Versus ambient temperature

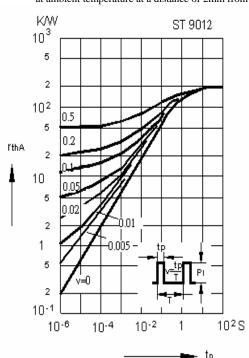
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



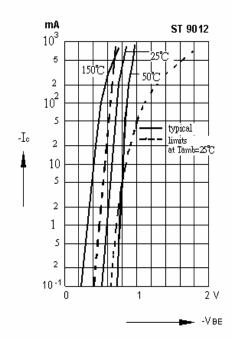
## **Pulse thermal resistance** versus pulse duration

Valid provided that leads are kept

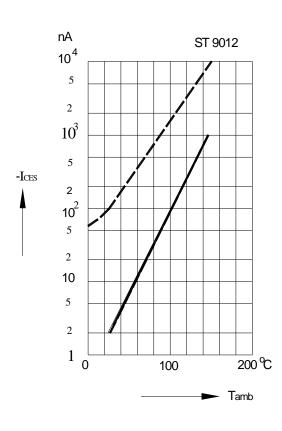
at ambient temperature at a distance of 2mm from



#### Collector current versus base emitter voltage



### Collector cutoff current versus ambient temperature





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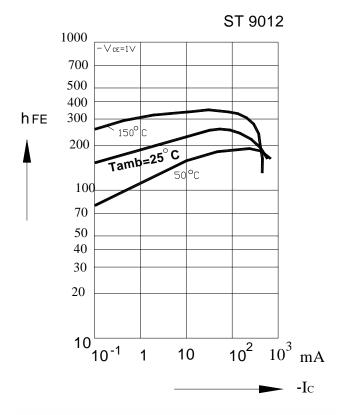
(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



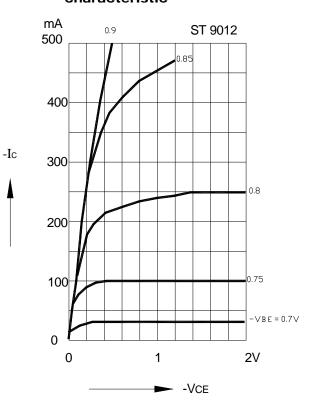




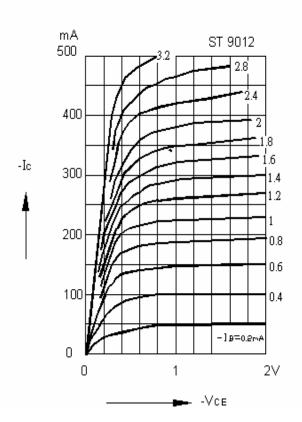
### DC current gain versus collector current



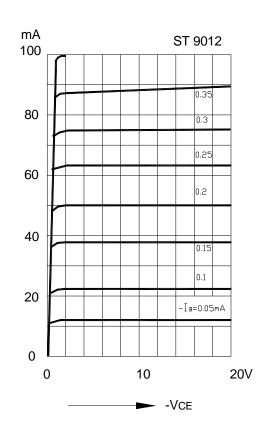
## Common emitter collector characteristic



### Common emitter collector characteristics



### **Common emitter** collector characteristics



-Ic



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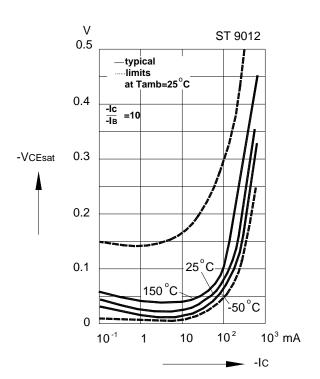
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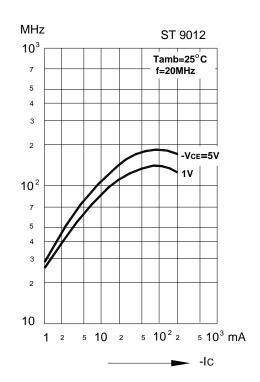


### Collector saturation voltage versus collector current

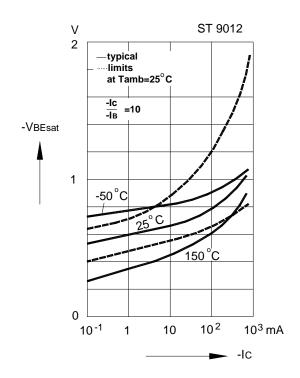


### **Gain bandwith product** versus collector current

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### Base saturation voltage versus collector current





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